

FEATURES

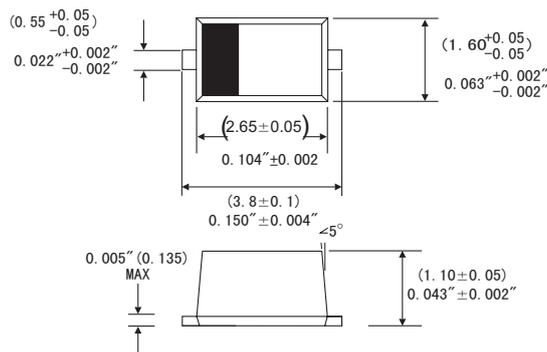
- Total power dissipation: max. 500 mW
- Small plastic package suitable for surface mounted design
- Wide variety of voltage ranges:
nom. 2.0 to 120V (E24 range)
- Tolerance approximately $\pm 5\%$
- High temperature soldering guaranteed: 260°C/10 seconds at terminals
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



MECHANICAL DATA

- Case: SOD-123 plastic case
- Weight: Approx. 0.01 gram

SOD-123



ABSOLUTE MAXIMUM RATINGS(LIMITING VALUES) (TA=25°C)

	Symbols	Value	Units
Zener current see table "Characteristics"			
Power dissipation	P _{tot}	500	mW
Junction temperature	T _J	150	°C
Storage temperature range	T _{STG}	-55 to+150	°C

ELECTRICAL CHARACTERISTICS (TA=25°C)

	Symbols	Min	Typ	Max	Units
Thermal resistance junction to ambient	R _{θJA}			340	K/W
Forward voltage at I _F =10mA	V _F			0.9	V

1) Valid provided that a distance of 8mm from case is kept at ambient temperature

MM1Z... SILICON PLANAR ZENER DIODES

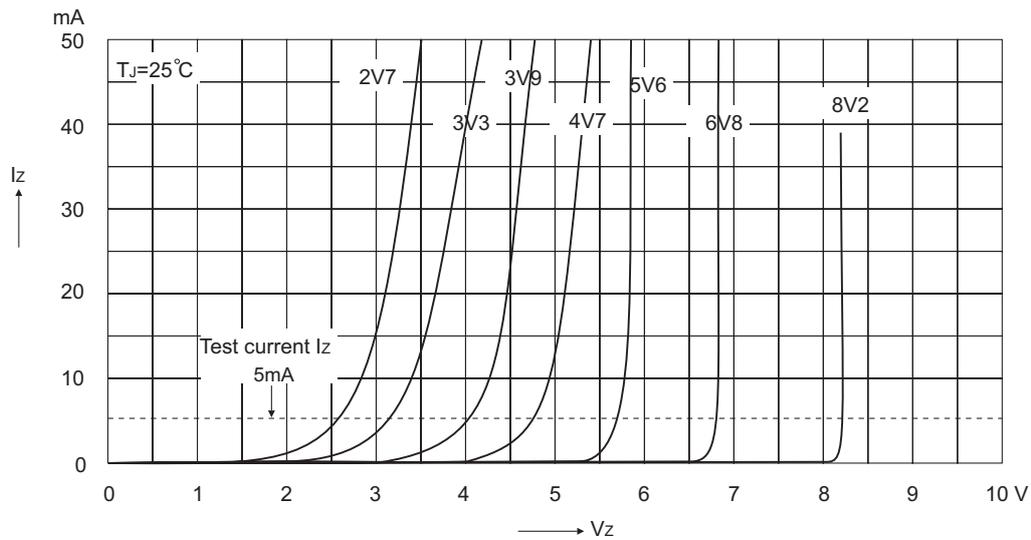
Type	Marking Code	Zener Voltage range ¹⁾			Dynamic resistance ²⁾		Reverse leakage current		Temp Coefficient of zener voltage
		V _{ZNOM}	I _{ZT} for V _{ZT}		r _{ZK} and r _{ZJK} at I _{ZK}		I _R	at V _R	TK _{VZ}
		V	mA	V	Ω	mA	μA	V	%/K
MM1Z 2V0	4A	2.0	5	1.80...2.15	100	5	120	0.5	-0.09...-0.06
MM1Z 2V2	4B	2.2	5	2.08...2.33	100	5	120	0.7	-0.09...-0.06
MM1Z 2V4	4C	2.4	5	2.28...2.56	100	5	120	1.0	-0.09...-0.06
MM1Z 2V7	4D	2.7	5	2.5...2.9	110	5	120	1.0	-0.09...-0.06
MM1Z 3V0	4E	3.0	5	2.8...3.2	120	5	50	1.0	-0.08...-0.05
MM1Z 3V3	4F	3.3	5	3.1...3.5	130	5	20	1.0	-0.08...-0.05
MM1Z 3V6	4H	3.6	5	3.4...3.8	130	5	10	1.0	-0.08...-0.05
MM1Z 3V9	4J	3.9	5	3.7...4.1	130	5	5	1.0	-0.08...-0.05
MM1Z 4V3	4K	4.3	5	4.0...4.6	130	5	5	1.0	-0.06...-0.03
MM1Z 4V7	4M	4.7	5	4.4...5.0	130	5	2	1.0	-0.05...+0.02
MM1Z 5V1	4N	5.1	5	4.8...5.4	130	5	2	1.5	-0.02...+0.02
MM1Z 5V6	4P	5.6	5	5.2...6.0	80	5	1	2.5	-0.05...+0.05
MM1Z 6V2	4R	6.2	5	5.8...6.6	50	5	1	3.0	0.03...0.06
MM1Z 6V8	4X	6.8	5	6.4...7.2	30	5	0.5	3.5	0.03...0.07
MM1Z 7V5	4Y	7.5	5	7.0...7.9	30	5	0.5	4.0	0.03...0.07
MM1Z 8V2	4Z	8.2	5	7.7...8.7	30	5	0.5	5.0	0.03...0.08
MM1Z 9V1	5A	9.1	5	8.5...9.6	30	5	0.5	6.0	0.03...0.09
MM1Z 10	5B	10	5	9.4...10.6	30	5	0.1	7.0	0.03...0.1
MM1Z 11	5C	11	5	10.4...11.6	30	5	0.1	8.0	0.03...0.11
MM1Z 12	5D	12	5	11.4...12.7	35	5	0.1	9.0	0.03...0.11
MM1Z 13	5E	13	5	12.4...14.1	35	5	0.1	10	0.03...0.11
MM1Z 15	5F	15	5	13.8...15.6	40	5	0.1	11	0.03...0.11
MM1Z 16	5H	16	5	15.3...17.1	40	5	0.1	12	0.03...0.11
MM1Z 18	5J	18	5	16.8...19.1	45	5	0.1	13	0.03...0.11
MM1Z 20	5K	20	5	18.8...21.2	50	5	0.1	15	0.03...0.11
MM1Z 22	5M	22	5	20.8...23.3	55	5	0.1	17	0.04...0.12
MM1Z 24	5N	24	5	22.8...25.6	60	5	0.1	19	0.04...0.12
MM1Z 27	5P	27	5	25.1...28.9	70	2	0.1	21	0.04...0.12
MM1Z 30	5R	30	5	28...32	80	2	0.1	23	0.04...0.12
MM1Z 33	5X	33	5	31...35	80	2	0.1	25	0.04...0.12
MM1Z 36	5Y	36	5	34...38	90	2	0.1	27	0.04...0.12
MM1Z 39	5Z	39	2.5	37...41	100	2	2	30	0.04...0.12
MM1Z 43	6A	43	2.5	40...46	130	2	2	33	0.04...0.12
MM1Z 47	6B	47	2.5	44...50	150	2	2	36	0.04...0.12
MM1Z 51	6C	51	2.5	48...54	180	2	1	39	0.04...0.12
MM1Z 56	6D	56	2.5	52...60	180	2	1	43	0.04...0.12
MM1Z 62	6E	62	2.5	58...66	200	2	0.2	47	0.04...0.12
MM1Z 68	6F	68	2.5	64...72	250	2	0.2	52	0.04...0.12
MM1Z 75	6H	75	2.5	70...79	300	2	0.2	57	0.04...0.12
MM1Z 82	6J	82	2.5	77...87	300	2	0.2	63	0.05...0.12
MM1Z 91	6K	91	1	85...96	700	1	0.2	69	0.05...0.12
MM1Z 100	6M	100	1	94...106	700	1	0.2	76	0.05...0.12
MM1Z 110	6N	110	1	104...116	800	1	0.2	84	0.05...0.12
MM1Z 120	6P	120	1	114...127	900	1	0.2	91	0.05...0.12

1) Tested with pulses tp=20ms.

2) Z_z is measured at I_z by given a very small A. C. current signal.

MM1Z... SILICON PLANAR ZENER DIODES

BREAKDOWN CHARACTERISTICS AT $T_J = \text{CONSTANT}$ (PULSED)



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